New Jersey Semi-Conductor Products, Inc.

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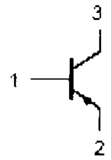
Silicon PNP Power Transistor

2SA808

DESCRIPTION

- High Power Dissipation-
  : P_C= 50W(Max.)@T_C=25℃
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -80V(Min.)



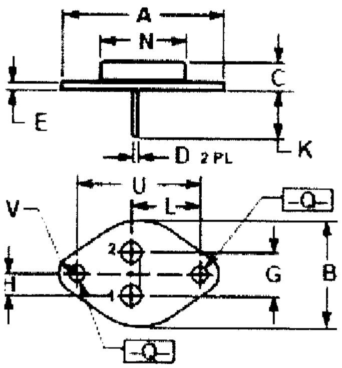
PIN 1. BASE
2. EMITTER
3. COLLECTOR (CASE)
TO-3 package

APPLICATIONS

- Designed for general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-6	A
I_B	Base Current-Continuous	-3	A
P_C	Collector Power Dissipation @T_C=25℃	50	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃



DIM	mm	
	MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

Quality Semi-Conductors

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA ;I_B= 0	-80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.3A			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -80V; I_E= 0			-1.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0			-1.0	mA
h_{FE}	DC Current Gain	I_C= -3A; V_{CE}= -4V	20			
f_T	Current-Gain—Bandwidth Product	I_E= 0.5A; V_{CE}= -12V		10		MHz

Switching times

t_r	Rise Time	I_C= -3A ,R_L= 3Ω , V_{CC}= -10V I_{B1}= -0.3A; I_{B2}= 50mA		1.2		μ s
t_{stg}	Storage Time			1.8		μ s
t_f	Fall Time			0.3		μ s